

FEATURES

- **HIGH POWER**
P1dB=33.0dBm at 3.4GHz to 5.1GHz
- **BROAD BAND INTERNALLY MATCHED**
- **HIGH GAIN**
G1dB=22.0dB at 3.4GHz to 5.1GHz
- **HERMETICALLY SEALED PACKAGE**

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	25
Flange Temperature	Tf	°C	-30 ~ +80
Storage Temperature	Tstg	°C	-65 ~ +175

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDD1=VDD2=VDD3 = 10V VGG= -5V f = 3.4 – 5.1GHz	dBm	32.0	33.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	20.0	22.0	—
Drain Current*	IDD		A	—	1.6	1.9
Input VSWR	VSWRin		—	—	—	3.0

* IDD = IDD1 + IDD2 + IDD3

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